InGaP HBT ACTIVE BIAS

MMIC AMPLIFIER, 0.05 - 3 GHz

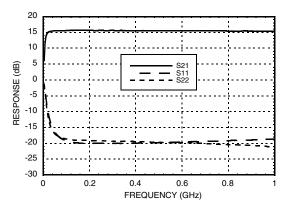


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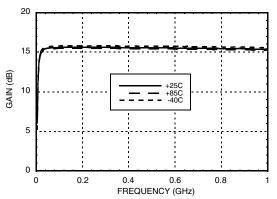


#### IF Band Performance

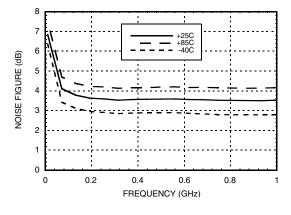
#### Gain & Return Loss



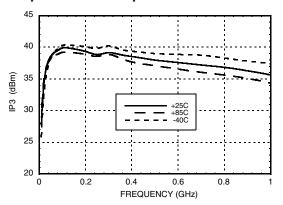
# Gain vs. Temperature



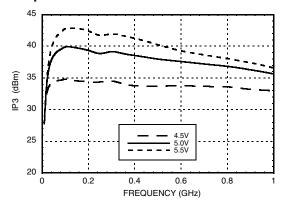
# Noise Figure vs. Temperature



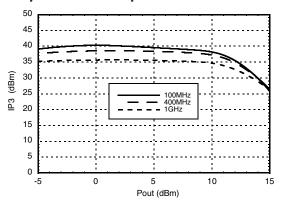
#### Output IP3 vs. Temperature



### Output IP3 vs. Vcc



#### Output IP3 vs. Output Power



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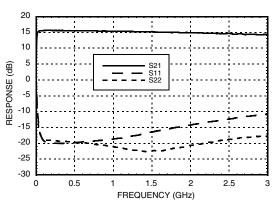




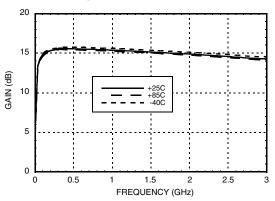
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#### **Broadband Performance**

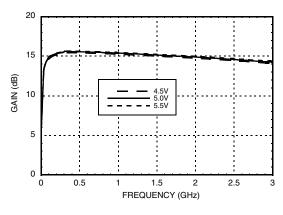
#### Gain & Return Loss



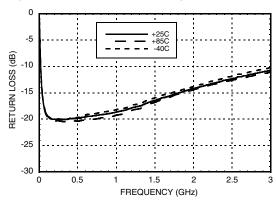
## Gain vs. Temperature



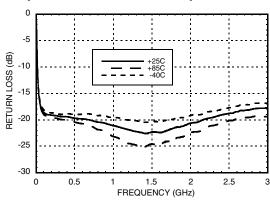
#### Gain vs. Vcc



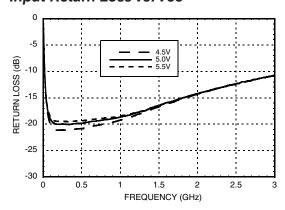
## Input Return Loss vs. Temperature



### Output Return Loss vs. Temperature



### Input Return Loss vs. Vcc



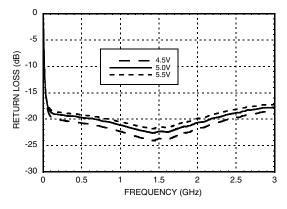
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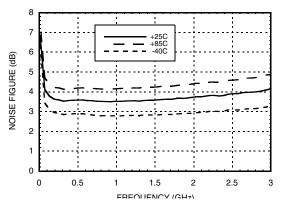


# InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

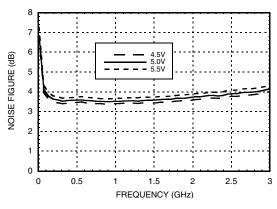
## **Output Return Loss vs. Vcc**



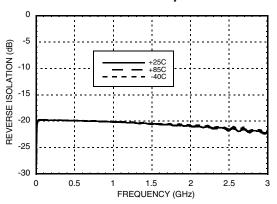
## Noise Figure vs. Temperature



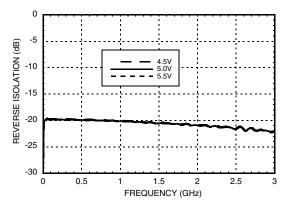
# Noise Figure vs. Vcc



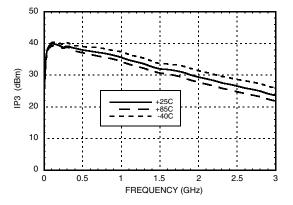
#### Reverse Isolation vs. Temperature



### Reverse Isolation vs. Vcc



## **Output IP3 vs. Temperature**



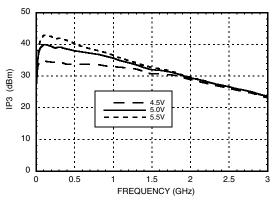
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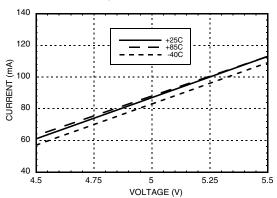


# InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

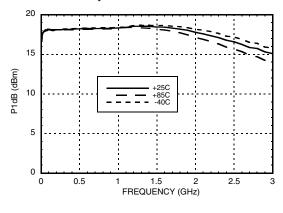
# Output IP3 vs. Vcc



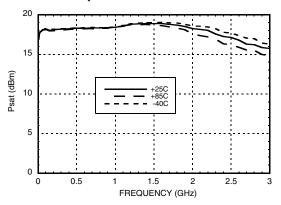
## Current vs. Temperature



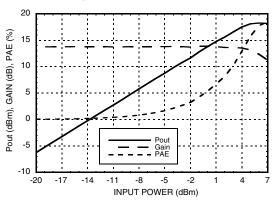
#### P1dB vs. Temperature



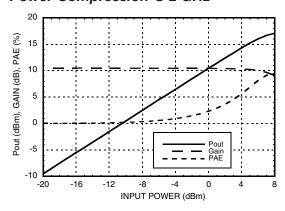
#### Psat vs. Temperature



## Power Compression @ 500 MHz



#### **Power Compression @ 2 GHz**



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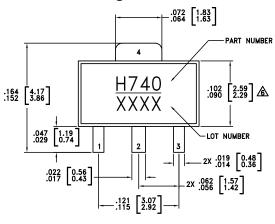
# InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

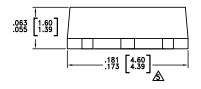
# **Absolute Maximum Ratings**

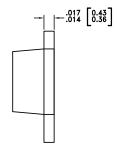
| Collector Bias Voltage (Vcc)                                     | +5.5 Vdc       |  |
|--|----------------|--|
| RF Input Power (RFIN)  | +15 dBm        |  |
| Junction Temperature   | 150 °C         |  |
| Continuous Pdiss (T = 85 °C)<br>(derate 10.23 mW/°C above 85 °C) | 0.66 W         |  |
| Thermal Resistance (junction to lead)                            | 97.78 °C/W     |  |
| Storage Temperature  | -65 to +150 °C |  |
| Operating Temperature  | -40 to +85 °C  |  |
| ESD Sensitivity (HMB)  | Class 1C       |  |

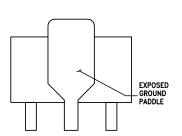


# **Outline Drawing**









#### NOTES:

- 1. PACKAGE BODY MATERIAL:
- MOLDING COMPOUND MP-180S OR EQUIVALENT.
- 2. LEAD MATERIAL: Cu w/ Ag SPOT PLATING.
- 3. LEAD PLATING: 100% MATTE TIN.
- 4. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- 7. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

# Package Information

|             | Part Number | Package Body Material                              | Lead Finish   | MSL Rating | Package Marking [1] |
|-------------|-------------|--|---------------|------------|---------------------|
| HMC740ST89E |             | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 [2]   | <u>H740</u><br>XXXX |

<sup>[1] 4-</sup>Digit lot number XXXX

[2] Max peak reflow temperature of 260 °C



RoHSV

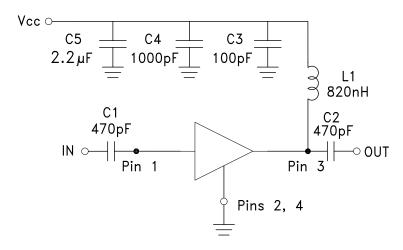
# InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

### **Pin Descriptions**

| Pin Number | Function | Description   | Interface Schematic |  |
|------------|----------|---|---------------------|--|
| 1          | IN       | This pin is DC coupled.<br>An off chip DC blocking capacitor is required. | OUT                 |  |
| 3          | ОИТ      | RF output and DC Bias (Vcc) for the output stage.                         |                     |  |
| 2, 4       | GND      | These pins and package bottom must be connected to RF/DC ground.          | O GND               |  |

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# **Application Circuit**

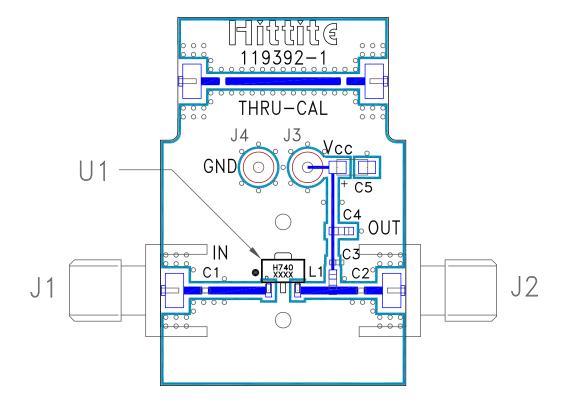






# InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

#### **Evaluation PCB**



#### List of Materials for Evaluation PCB 124390 [1]

| Item    | Description   |  |
|---------|---|--|
| J1, J2  | PCB Mount SMA Connector   |  |
| J3, J4  | DC Pin  470 pF Capacitor, 0402 Pkg.  100 pF Capacitor, 0402 Pkg.  1000 pF Capacitor, 0603 Pkg.  2.2 µF Capacitor Tantalum  820 nH Inductor, 0603 Pkg. |  |
| C1, C2  |   |  |
| C3      |   |  |
| C4      |   |  |
| C5      |   |  |
| L1      |   |  |
| U1      | HMC740ST89E   |  |
| PCB [2] | 119392 Evaluation PCB   |  |

<sup>[1]</sup> Reference this number when ordering complete evaluation PCB

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

<sup>[2]</sup> Circuit Board Material: FR4